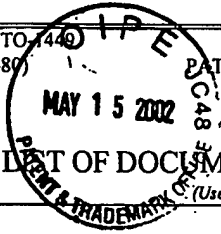


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Sheet 1 of 1

FORM PTO-440 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TI-24742		SERIAL NO. 09/176,422	
				LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)			
APPLICANT Wilk et al.				FILING DATE 10/21/98		GROUP 2823	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	AA						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	BA						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
NB	CA	Nayar, et al., "Chemically Treated Stepped Silicon {100} Surfaces," Proceedings of the International Symposium on the Ultra-Clean Processing of Silicon Surfaces, 19 September 1994, pp. 371-374 (VISHAL NAYAR, ALLAN J. PIDDUCK, MOHAMMED IDREES and BEVERLEY E.J. DEW)					
NB	CB	V. Nayar, et al., "Atmospheric Pressure, Low Temperature (<500°C) UV/Ozone Oxidation of Silicon," Electronic Letters, 1 February 1990, Vol. 26, No. 3, pp. 205-206 (V. NAYAR, P. PATEL, IAN W. BOYD)					
NB	CC	Morita, et al., "Effects of Si Wafer Surface Micro-Roughness on Electrical Properties of Very-Thin Gate Oxide Films," Proceedings of the International Symposium on Ultra Large Scale Integration Science and Technology, Pennington, NJ, 5 May 1991, pp. 400-408 (M. MORITA, A. TERAMOTO, K. MAKIHARA, and T. OHMI)					
NB	CD	Wilk, et al., "In Situ Si Flux Cleaning Technique for Producing Atomically Flat Si(100) Surfaces at Low Temperature," Appl. Phys. Lett. 70, 28 April 1997, pp. 2288-2290 (G.D. WILK, YI WEI, HAL EDWARDS, and R.M. WALLACE)					
NB	CE	Chin, et al., "Thin Oxides With In-Situ Native Oxide Removal," IEEE Electron Device Letters, IEEE Inc. New York, Vol. 18, No. 9, 1 September 1997, pp. 417-419 (ALBERT CHIN, SENIOR MEMBER IEEE, W. J. CHEN, T. CHANG, R.H. KAO, B.C. LIN, TSAI and J.C.-M HUANG)					
NB	CF	Froeschle, et al., "Cleaning Process Optimization in a Gate Oxide Cluster Tool Using an In-Line XPS Module," Mat. Res. Soc. Symp., Proc. Vol. 477, 1 April 1997, pp. 371-377 (BARBARA FROESCHLE, FREDERIQUE GLOWACKI, ANTON J. BAUER, IGOR KASKO, RICHARD OECHSNER and CLAUS SCHNEIDER)					
NB	CG	Nakanishi, et al., "Ultrathin Oxides by UV/Ozone Pretreatment Cleaning and Ozone Oxidation," Proceedings of the International Symposium of the Physics and Chemistry of SiO ₂ and the Si-SiO ₂ Interface, Vol. 96, No. 1, 5 May 1996, pp. 316-328 (TOSHIRO NAKANISHI, SATOSHI OHKUBO, YASUYUKI TAMURA, RINJI SUGINO, NAOKI AWAJI, and KANETAKE TAKASAKI)					
NB	CH	Nayar, et al., "An Effective Oxidation Technique for the Formation of Thin SiO ₂ at <500°C," Insulating Films on Semiconductors 1991 Proceedings from the 7 th Biennial European Conference Including Satellite Workshops on Silicon on Insulator: Materials and Device Technology and the Physics of Hot Electron Degradation in Si Mosfets Liverpool, pp. 163-166 (VISHAL NAYAR and IAN W. BOYD)					
NB	CI	Nakanishi, et al., "Oxidation in Ozone," Fujitsu-Scientific and Technical Journal, Fujitsu Limited, Kawasaki, JP, Vol. 32, No. 1, 1 June 1996, pp. 128-131 (TOSHIRO NAKANISHI, SATOSHI OHKUBO and YASUYUKI TAMURA)					
EXAMINER Neal Berzmy				DATE CONSIDERED 7/26/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							